

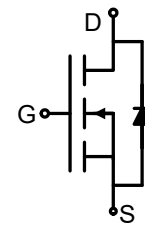
## NCE N-Channel Enhancement Mode Power MOSFET

### Description

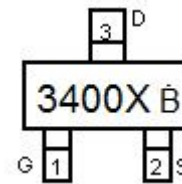
The NCE3400X uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

- $V_{DS} = 30V, I_D = 5.1A$ 
  - $R_{DS(ON)} < 55m\Omega @ V_{GS}=2.5V$
  - $R_{DS(ON)} < 39m\Omega @ V_{GS}=4.5V$
  - $R_{DS(ON)} < 33m\Omega @ V_{GS}=10V$
- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3400X B	NCE3400X	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	5.1	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	20	A
Maximum Power Dissipation	$P_D$	1.3	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	96	$^\circ C/W$
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### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$	-	-	1	$\mu A$

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.7	0.9	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=3A$	-	33	55	m $\Omega$
		$V_{GS}=4.5V, I_D=4A$	-	26	39	m $\Omega$
		$V_{GS}=10V, I_D=5A$	-	24	33	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=5A$	-	10	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	595	-	PF
Output Capacitance	$C_{oss}$		-	39	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	36	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	3.0	-	nS
Turn-on Rise Time	$t_r$		-	4.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	nS
Turn-Off Fall Time	$t_f$		-	3.8	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=5A,$ $V_{GS}=4.5V$	-	9.3	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.6	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.1	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	5.1	A

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## Typical Electrical and Thermal Characteristics

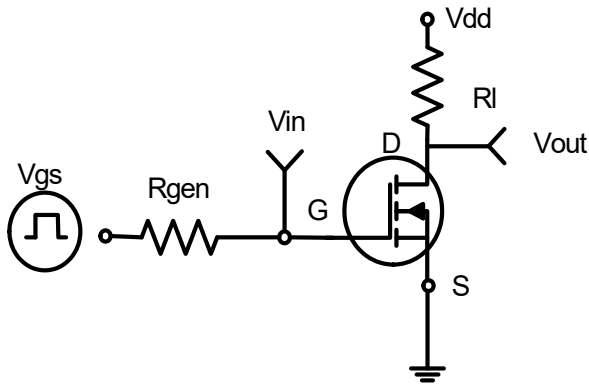


Figure 1: Switching Test Circuit

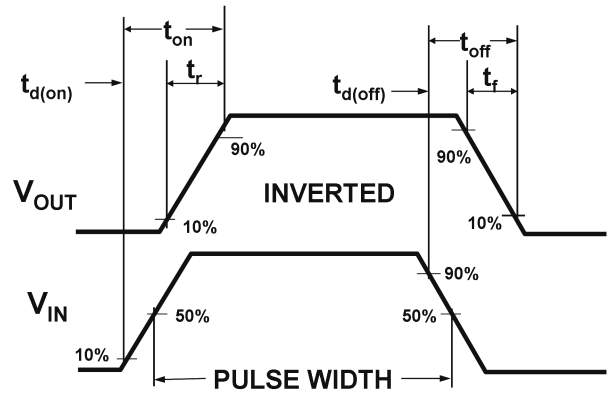
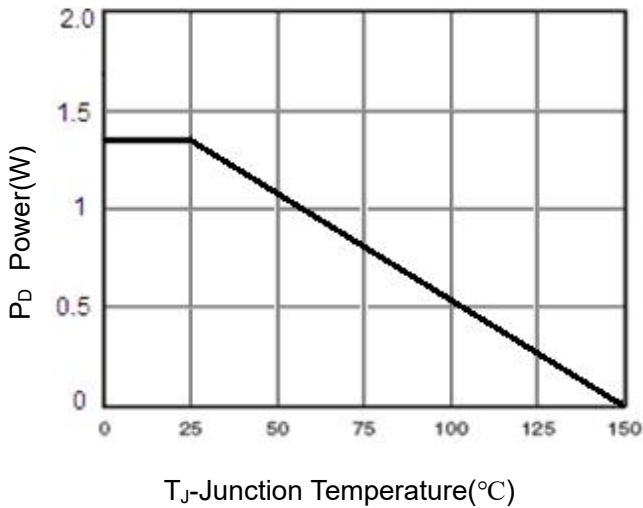
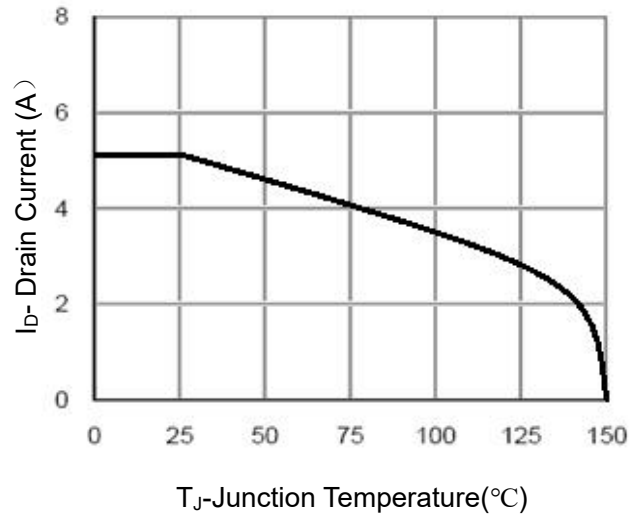


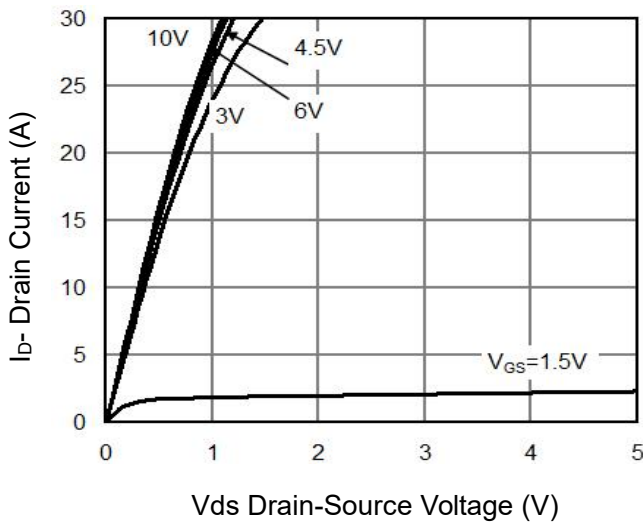
Figure 2: Switching Waveforms



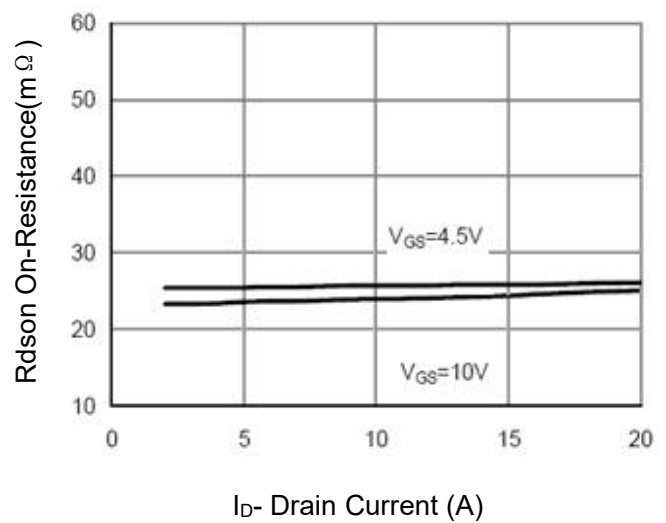
T<sub>J</sub>-Junction Temperature(°C)  
Figure 3 Power Dissipation



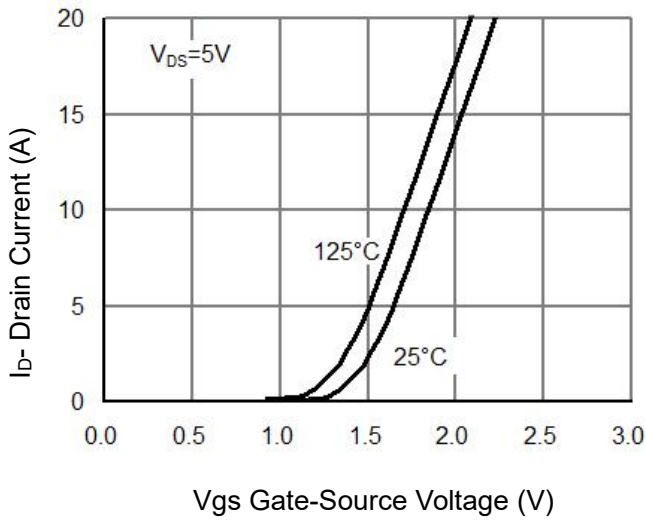
T<sub>J</sub>-Junction Temperature(°C)  
Figure 4 Drain Current



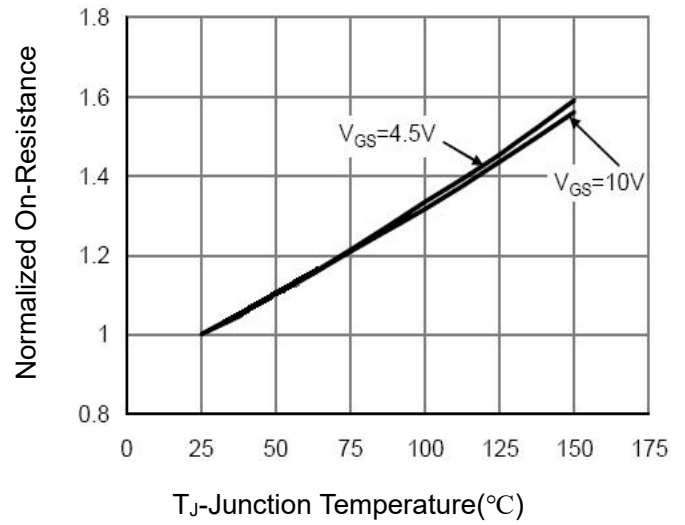
V<sub>ds</sub> Drain-Source Voltage (V)  
Figure 5 Output Characteristics



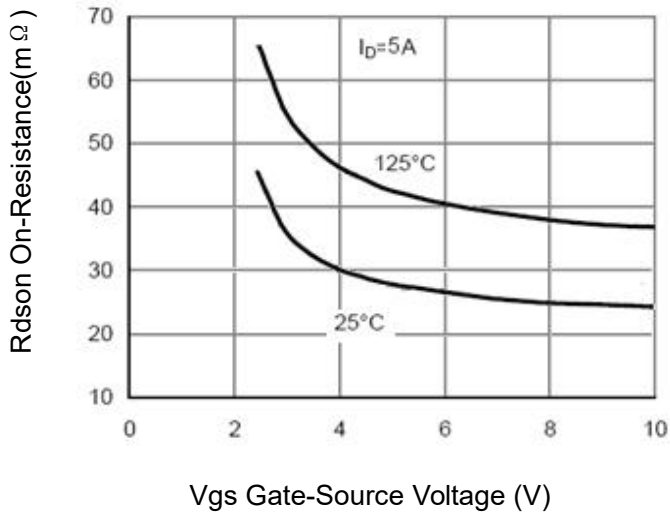
I<sub>D</sub>- Drain Current (A)  
Figure 6 Drain-Source On-Resistance



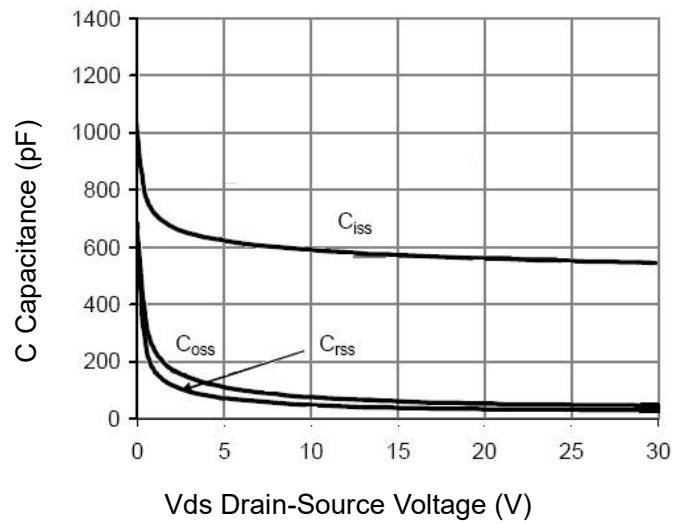
**Figure 7 Transfer Characteristics**



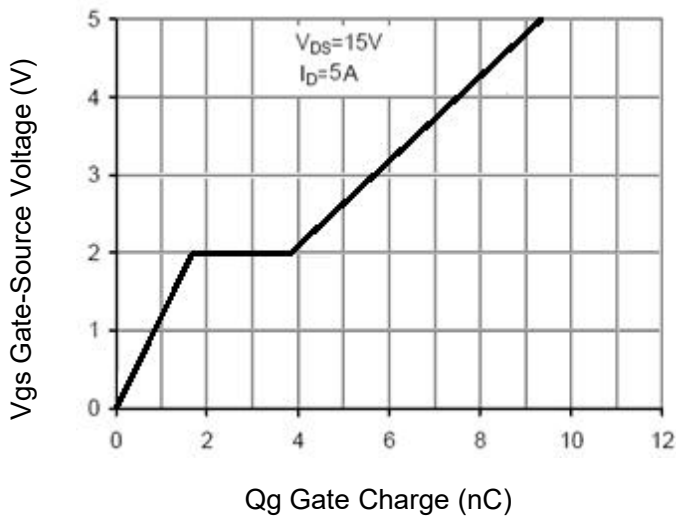
**Figure 8 Drain-Source On-Resistance**



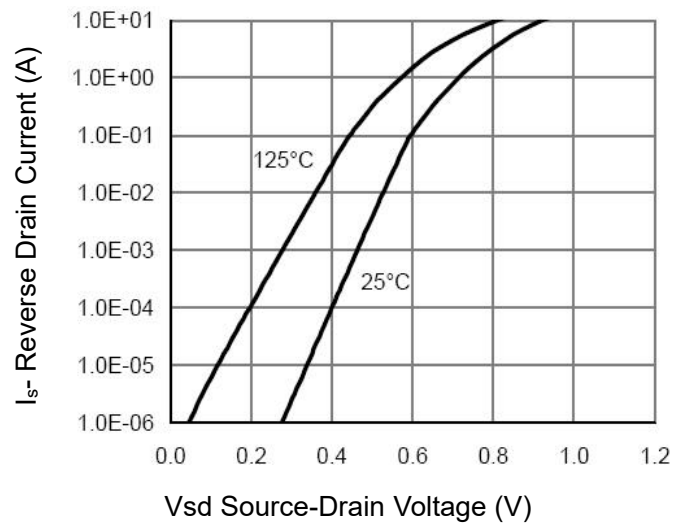
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**



**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**

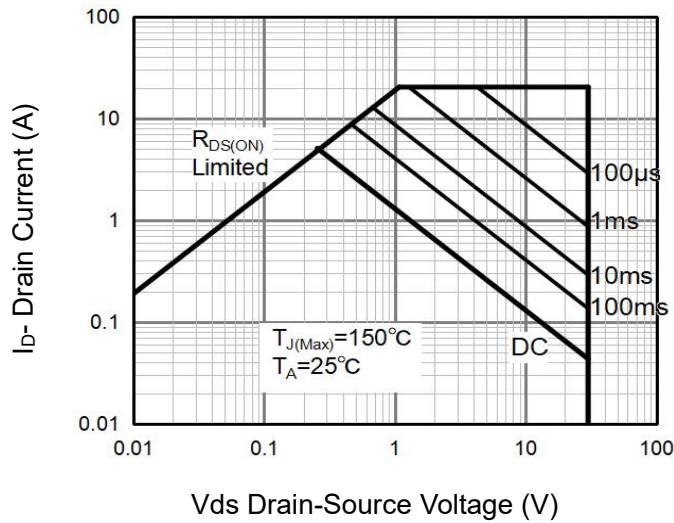


Figure 13 Safe Operation Area

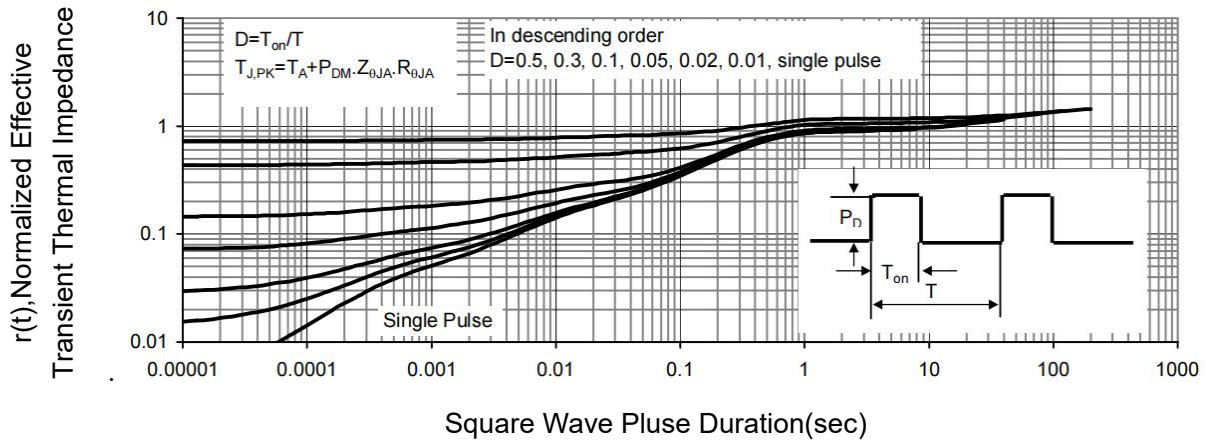
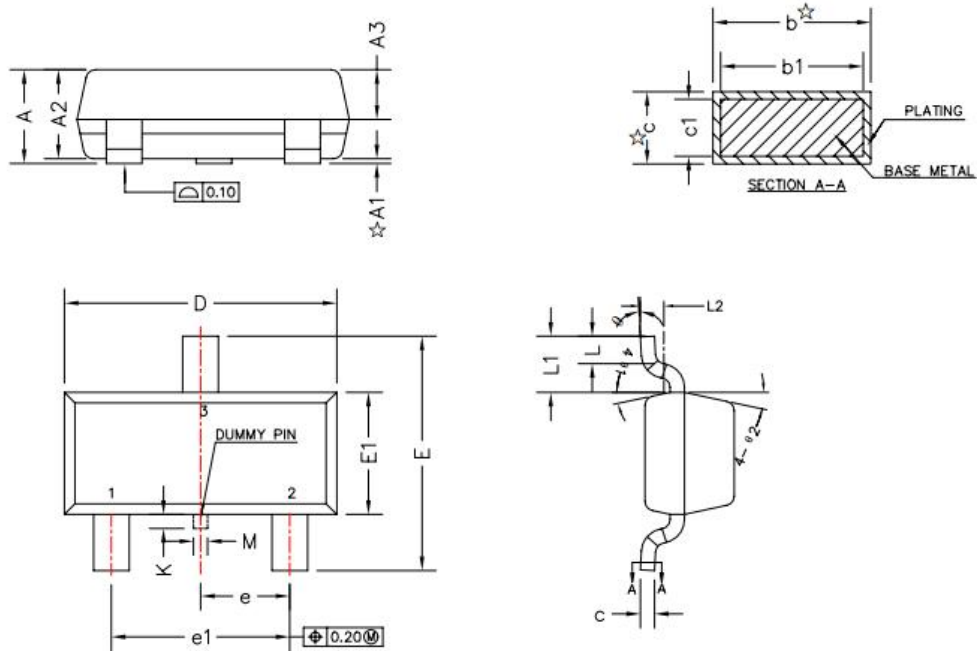


Figure 14 Normalized Maximum Transient Thermal Impedance

## SOT-23 Package Information



Symbol	Millimeters	
	Min.	Max.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
A3	0.43	0.63
b	0.36	0.50
b1	0.35	0.45
c	0.14	0.20
c1	0.14	0.16
D	2.80	3.00
E	2.35	2.64
E1	1.20	1.40
e	0.90	1.00
e1	1.80	2.00
L	0.40	0.60
L1	0.6REF	
L2	0.25BSC	
M	0.10	0.25
K	0.00	0.25
$\theta$	0°	8°
$\theta_1$	10°	14°
$\theta_2$	10°	14°

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